BLC10G22XS-401AVT

Power LDMOS transistor

AMPLEON

Rev. 1 — 20 May 2022

Product data sheet

1. Product profile

1.1 General description

400 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 2110 MHz to 2200 MHz.

Table 1. Typical performance

Typical RF performance at $T_{case} = 25$ °C in an asymmetrical Doherty demo circuit. $V_{DS} = 30$ V; $I_{Dq} = 630$ mA (main); $V_{GS(amp)peak} = 0.8$ V, unless otherwise specified.

Test signal	f	V _{DS}	P _{L(AV)}	G _p	ησ	ACPR
	(MHz)	(V)	(W/dBm)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2110 to 2200	30	56/47.5	15.4	49.3	-30 [1]

Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.9 dB at 0.01 % probability on CCDF.

1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

1.3 Applications

 RF power amplifiers for base stations and multi carrier applications in the 2110 MHz to 2200 MHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simp	olified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)	5	1 2 6	1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]	5 4	amp01357

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC10G22XS-401AVT	-	air cavity plastic earless flanged package; 6 leads	SOT1275-1				

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage			-	65	٧
V _{GS(amp)main}	main amplifier gate-source voltage			-6	+9	V
V _{GS(amp)peak}	peak amplifier gate-source voltage			-6	+9	V
T _{stg}	storage temperature			-65	+150	°C
Tj	junction temperature		[1]	-	225	°C
T _{case}	case temperature	operating	[1]	-40	+125	°C

^[1] Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
	thermal resistance from junction to case	$V_{DS} = 30 \text{ V; } I_{Dq} = 580 \text{ mA (main);} $ $V_{GS(amp)peak} = 0.70 \text{ V; } T_{case} = 80 ^{\circ}\text{C}$		
		$P_L = 56 \text{ W}$	0.29	K/W
		P _L = 71 W	0.27	K/W

6. Characteristics

 Table 6.
 DC characteristics

 $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Main devi	ce					
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 1.3 \text{ mA}$	65	-	-	٧
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 131 \text{ mA}$	1.6	2.0	2.4	٧
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 30 \text{ V}; I_D = 776 \text{ mA}$	-	2.1	-	٧
I _{DSS}	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 32 \text{ V}$	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V}$	-	24	-	Α
I _{GSS}	gate leakage current	$V_{GS} = 9 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	140	nΑ
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; I_D = 4.585 \text{ A}$	-	13	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 4.585 \text{ A}$	-	99	170	mΩ
Peak devi	ice	1	'		'	
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.2 \text{ mA}$	65	-	-	٧
V _{GS(th)}	gate-source threshold voltage	$V_{DS} = 10 \text{ V}; I_D = 217 \text{ mA}$	1.6	2.0	2.4	٧
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 30 \text{ V}; I_D = 1100 \text{ mA}$	-	2.2	-	٧
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 32 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 2.37 \text{ V}$	-	38	-	Α
I _{GSS}	gate leakage current	V _{GS} = 9 V; V _{DS} = 0 V	-	-	140	nA
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 7.595 A	-	20	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 2.37 \text{ V};$ $I_D = 7.595 \text{ A}$	-	65	107	mΩ

Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2112.5 MHz; f_2 = 2197.5 MHz; RF performance at V_{DS} = 30 V; I_{Dq} = 776 mA (main); $V_{GS(amp)peak}$ = 0.770 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2110 MHz to 2200 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P _{L(AV)} = 56.2 W	14	15	-	dB
RLin	input return loss	P _{L(AV)} = 56.2 W	-	-17	-9	dB
η_{D}	drain efficiency	P _{L(AV)} = 56.2 W	44	48	-	%
ACPR	adjacent channel power ratio	P _{L(AV)} = 56.2 W	-	-29	-25	dBc

Table 8. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 9.6 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH; f_1 = 2112.5 MHz; f_2 = 2197.5 MHz; RF performance at V_{DS} = 30 V; I_{Dq} = 776 mA (main); $V_{GS(amp)peak}$ = 0.770 V; T_{case} = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2110 MHz to 2200 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
PARO	output peak-to-average ratio	$P_{L(AV)} = 89.1 \text{ W}$	5.9	6.5	-	dB
$P_{L(M)}$	peak output power	P _{L(AV)} = 89.1 W	340	390	-	W

7. Test information

7.1 Ruggedness in Doherty operation

The BLC10G22XS-401AVT is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 776 mA; $V_{GS(amp)peak}$ = 0.74 V; f = 2210 MHz; P_L = 160 W (5 dB OBO); 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device; I_{Dq} = 650 mA (main); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]			
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)			
Maximum	Maximum power load							
2110	3.8 – j11.3	2.8 – j7.7	206	59.7	14.9			
2140	4.6 – j12.0	2.8 – j7.7	205	59.6	14.9			
2170	5.7 – j12.7	2.8 – j7.7	202	59.2	15.0			
Maximum	n drain efficiency	load						
2110	3.7 – j11.6	6.0 – j5.3	137	70.0	17.1			
2140	4.6 – j12.3	5.9 – j5.3	134	69.8	17.2			
2170	5.7 – j13.0	5.3 – j5.0	133	69.2	17.2			

^[1] Z_S and Z_L defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device; I_{Dq} = 1085 mA (peak); V_{DS} = 30 V; pulsed CW (t_p = 100 μ s; δ = 10 %).

f	Z _S [1]	Z _L [1]	P _L [2]	η _D [2]	G _p [2]			
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)			
Maximum	Maximum power load							
2110	4.2 – j9.5	6.3 – j6.8	305	57.7	15.6			
2140	5.4 – j9.4	6.3 – j6.8	303	57.5	15.7			
2170	6.7 – j8.7	6.3 – j6.8	300	57.3	15.8			
Maximum	drain efficiency	load						
2110	4.3 – j9.4	4.0 – j3.2	220	66.7	17.6			
2140	5.6 – j9.1	4.0 – j3.2	214	66.4	17.8			
2170	6.8 – j8.0	3.7 – j3.5	209	66.1	17.9			

^[1] Z_S and Z_L defined in <u>Figure 1</u>.

^[2] At 3 dB gain compression.

^[2] At 3 dB gain compression.



Fig 1. Definition of transistor impedance

7.3 Test circuit

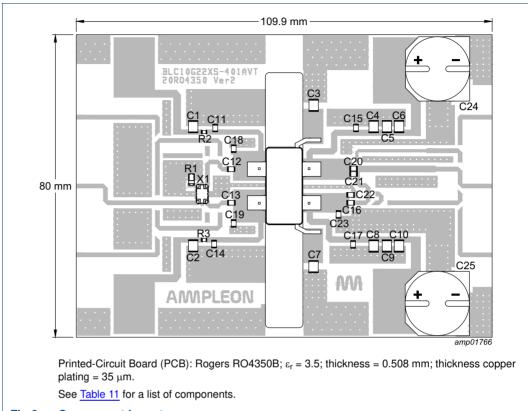


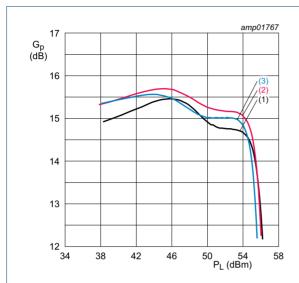
Fig 2. Component layout

Table 11. List of components For test circuit see Figure 2.

Component	Description	Value	Remarks
C1, C2, C3, C4, C5, C6, C7, C8, C9, C10	multilayer ceramic chip capacitor	10 μF, 100 V	Murata: GRM32EC72A106KE05L, SMD 1210
C11, C12, C13, C14, C15, C16, C17	multilayer ceramic chip capacitor	10 pF	Murata: GQM21 Hi-Q 250V series, SMD 0805
C18, C22, C23	multilayer ceramic chip capacitor	0.5 pF	Murata: GQM21 Hi-Q 250V series, SMD 0805
C19	multilayer ceramic chip capacitor	0.7 pF	Murata: GQM21 Hi-Q 250V series, SMD 0805
C20, C21	multilayer ceramic chip capacitor	3.3 pF	Murata: GQM21 Hi-Q 250V series, SMD 0805
C24, C25	electrolytic capacitor	470 μF, 63 V	Panasonic: EEVFK1J471M
R1	resistor	50 Ω, 8 W	Anaren: C8A50Z4B
R2, R3	resistor	5.1 Ω, 1 %	SMD 0603
X1	hybrid coupler	2 dB, 90°	Anaren: X3C20F1-02S

7.4 Graphical data

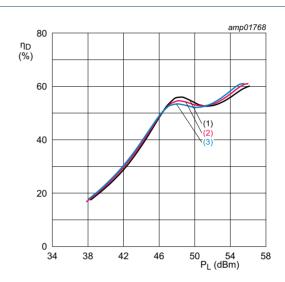
7.4.1 Pulsed CW



 V_{DS} = 30 V; I_{Dq} = 650 mA; $V_{GS(amp)peak}$ = 0.745 V; t_p = 100 $\mu s;$ δ = 10 %.

- (1) f = 2110 MHz
- (2) f = 2155 MHz
- (3) f = 2200 MHz

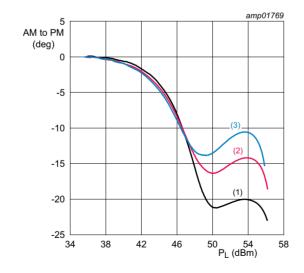
Fig 3. Power gain as a function of output power; typical values



 V_{DS} = 30 V; I_{Dq} = 650 mA; $V_{GS(amp)peak}$ = 0.745 V; t_p = 100 μ s; δ = 10 %.

- (1) f = 2110 MHz
- (2) f = 2155 MHz
- (3) f = 2200 MHz

Fig 4. Drain efficiency as a function of output power; typical values



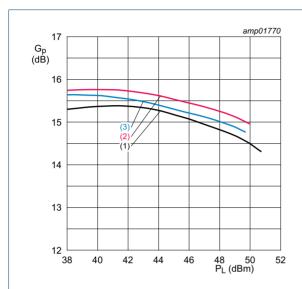
 $V_{DS} = 30 \text{ V}; I_{Dq} = 770 \text{ mA}; V_{GS(amp)peak} = 0.764 \text{ V}.$

- (1) f = 2110 MHz
- (2) f = 2155 MHz
- (3) f = 2200 MHz

Fig 5. Normalized AM to PM as a function of output power; typical values

7.4.2 1-Carrier W-CDMA

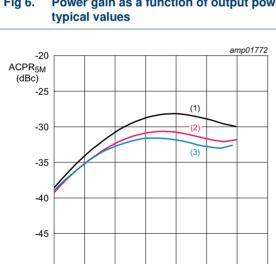
Test signal: 3GPP test model 1; 1 to 64 DPCH (100 % clipping); PAR = 9.9 dB at 0.01 % probability on CCDF per carrier.



 $V_{DS} = 30 \text{ V}; I_{Dq} = 770 \text{ mA}; V_{GS(amp)peak} = 0.764 \text{ V}.$

- (1) f = 2110 MHz
- (2) f = 2155 MHz
- (3) f = 2200 MHz

Power gain as a function of output power; Fig 6. typical values



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 $V_{DS} = 30 \text{ V}; I_{Dq} = 770 \text{ mA}; V_{GS(amp)peak} = 0.764 \text{ V}.$

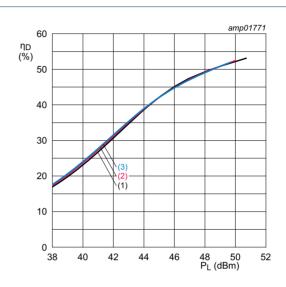
48 50 P_I (dBm)

(1) f = 2110 MHz

-50

- (2) f = 2155 MHz
- (3) f = 2200 MHz

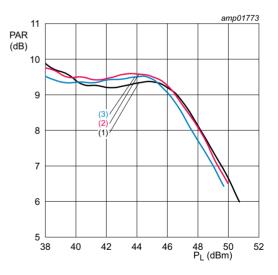
Fig 8. Adjacent channel power ratio (5 MHz) as a function of output power; typical values



 $V_{DS} = 30 \text{ V}$; $I_{Dq} = 770 \text{ mA}$; $V_{GS(amp)peak} = 0.764 \text{ V}$.

- (1) f = 2110 MHz
- (2) f = 2155 MHz
- (3) f = 2200 MHz

Drain efficiency as a function of output power; Fig 7. typical values



 $V_{DS} = 30 \text{ V}; I_{Dq} = 770 \text{ mA}; V_{GS(amp)peak} = 0.764 \text{ V}.$

- (1) f = 2110 MHz
- (2) f = 2155 MHz
- (3) f = 2200 MHz

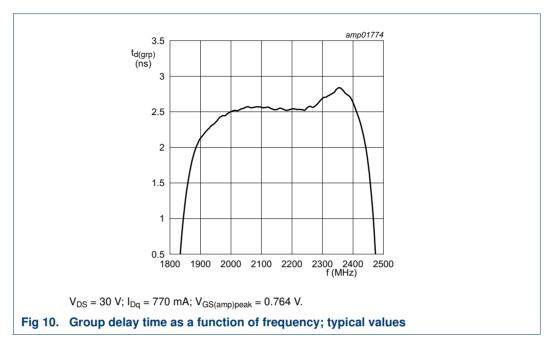
Peak-to-average power ratio as a function of Fig 9. output power; typical values

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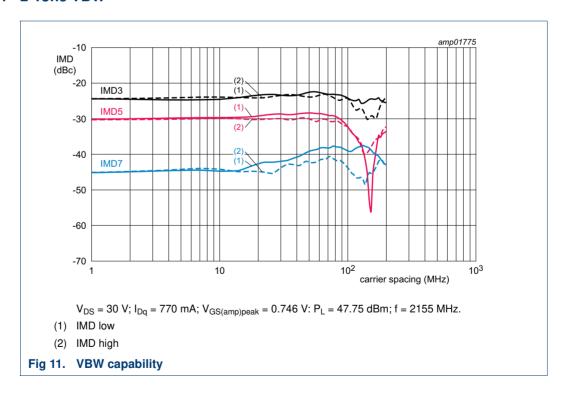
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7.4.3 Group delay



7.4.4 2-Tone VBW



8. Package outline

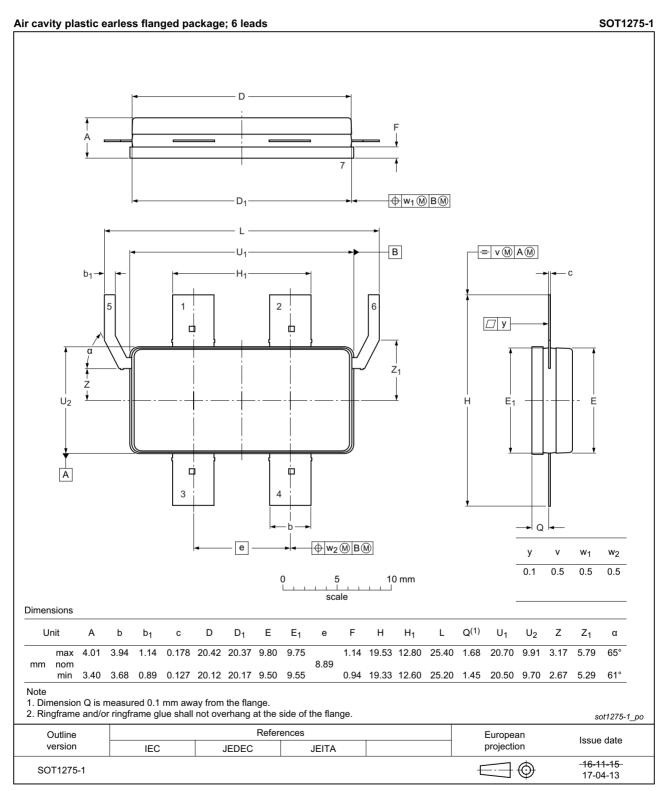


Fig 12. Package outline SOT1275-1

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C3 [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 🔼

- [1] CDM classification C3 is granted to any part that passes after exposure to an ESD pulse of 1000 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

10. Abbreviations

Table 13. Abbreviations

Table 10. Abbreviations				
Acronym	Description			
3GPP	3rd Generation Partnership Project			
AM	Amplitude Modulation			
CCDF	Complementary Cumulative Distribution Function			
CW	Continuous Wave			
DPCH	Dedicated Physical CHannel			
ESD	ElectroStatic Discharge			
LDMOS	Laterally Diffused Metal-Oxide Semiconductor			
MTF	Median Time to Failure			
ОВО	Output Back Off			
PAR	Peak-to-Average Ratio			
PM	Phase Modulation			
RoHS	Restriction of Hazardous Substances			
SMD	Surface Mounted Device			
VBW	Video BandWidth			
VSWR	Voltage Standing Wave Ratio			
W-CDMA	Wideband Code Division Multiple Access			

11. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC10G22XS-401AVT v.1	20220522	Product data sheet	-	-

BLC10G22XS-401AVT

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